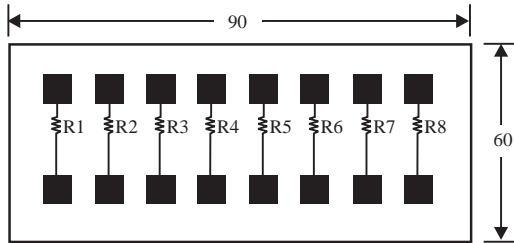




ISOLATED RESISTOR NETWORK

California Micro Devices' resistor arrays are the hybrid equivalent to the isolated resistor networks available in surface mount packages. The resistors are spaced on ten mil centers resulting in reduced real estate. These chips are manufactured using advanced thin film processing techniques and are 100% electrically tested and visually inspected.

ELECTRICAL SPECIFICATIONS			
Parameter	Test Condition		
TCR	-55°C to +125°	±100ppm/°C	Max
Operating Voltage	-55°C to +125°	50Vdc	Max
Power Rating (per resistor)	@ 70°C (Derate linearly to zero @ 150°C)	50mw	Max
Thermal Shock	Method 107 MIL-STD-202F	±0.25%ΔR	Max
High Temperature Exposure	100 Hrs @ 150°C Ambient	±0.25%ΔR	Max
Moisture Resistance	Method 106 MIL-STD-202F	±0.5%ΔR	Max
Life	Method 108 MIL-STD-202F (125°C/1000hr)	±0.5%ΔR	Max
Noise	Method 308 MIL-STD-202F	-35 dB	Max
	≥250kΩ	-30 dB	Max
Short Time Overload	MIL-R-83401	0.25%	Max
Insulation Resistance	@25°C	1 X 10 ¹² Ω	Min



VALUES
8 resistors from 100Ω to 346Ω

MECHANICAL SPECIFICATIONS	
Substrate	Silicon 10±2 mils thick
Isolation Layer	SiO ₂ 10,000Å thick, min
Backing	Lapped (gold optional)
Metalization	Aluminum 10,000Å thick, min (15,000Å gold optional)
Passivation	Silicon nitride

Formats

Die Size: 90±3 x 60±3 mils
Bonding Pads: 5x7 mils typical

PACKAGING
Two inch square trays of 196 chips maximum.

NOTES
1. Resistor pattern may vary from one value to another.

PART NUMBER DESIGNATION N						
CC	5003	F	A	G	W	P
Series	Value First 3 digits are significant value. Last digit represents number of zeroes. R indicates decimal point.	Tolerance D = ±0.5% F = ±1% G = ±2% J = ±5% K = ±10% M = ±20%	TCR No Letter = ±100ppm A = ±50% B = ±25%	Bond Pads G = Gold No Letter = Aluminum	Backing W = Gold L = Lapped No Letter = Either	Ratio Tolerance No Letter = ±1% P = ±0.5%